

October 2014

### FDMS86200

# N-Channel Shielded Gate PowerTrench<sup>®</sup> MOSFET 150 V, 35 A, 18 m $\Omega$

#### **Features**

- Shielded Gate MOSFET Technology
- Max  $r_{DS(on)} = 18 \text{ m}\Omega$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 9.6 \text{ A}$
- Max  $r_{DS(on)} = 21 \text{ m}\Omega$  at  $V_{GS} = 6 \text{ V}$ ,  $I_D = 8.8 \text{ A}$
- Advanced Package and Silicon combination for low r<sub>DS(on)</sub> and high efficiency
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

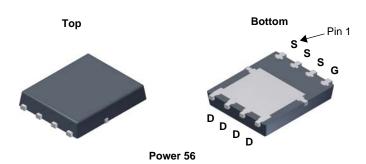


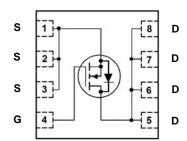
#### **General Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and yet maintain superior switching performance.

#### **Application**

■ DC-DC Conversion





### **MOSFET Maximum Ratings** $T_A = 25 \, ^{\circ}\text{C}$ unless otherwise noted

Symbol	Parame	Parameter			Units
V <sub>DS</sub>	Drain to Source Voltage			150	V
V <sub>GS</sub>	Gate to Source Voltage			±20	V
	Drain Current -Continuous	T <sub>C</sub> = 25 °C		35	
I <sub>D</sub>	-Continuous	T <sub>A</sub> = 25 °C	(Note 1a)	9.6	Α
	-Pulsed			100	
E <sub>AS</sub>	Single Pulse Avalanche Energy		(Note 3)	220	mJ
D	Power Dissipation	T <sub>C</sub> = 25 °C		104	W
$P_{D}$	Power Dissipation	T <sub>A</sub> = 25 °C	(Note 1a)	2.5	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Tempera	ture Range		-55 to +150	°C

#### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note	a) 50	- C/VV

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS86200	FDMS86200	Power 56	13 "	12 mm	3000 units

### **Electrical Characteristics** $T_J = 25 \, ^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25 °C		110		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V			1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA

#### **On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2.0	2.5	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25 °C		-10		mV/°C
		$V_{GS} = 10 \text{ V}, I_D = 9.6 \text{ A}$		15	18	
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 6 \text{ V}, I_D = 8.8 \text{ A}$		17	21	mΩ
, ,		$V_{GS} = 10 \text{ V}, I_D = 9.6 \text{ A}, T_J = 125 ^{\circ}\text{C}$		28	34	
g <sub>FS</sub>	Forward Transconductance	$V_{DD} = 10 \text{ V}, I_D = 9.6 \text{ A}$		33		S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 75 V V 0 V	2041	2715	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 0 V, f = 1 MHz	203	270	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1011 12	10	16	pF
$R_g$	Gate Resistance		1.2	3	Ω

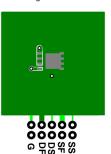
#### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time			13	23	ns
t <sub>r</sub>	Rise Time	$V_{DD} = 75 \text{ V}, I_{D} = 9.0$	6 A,	7.9	16	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> = 10 V, R <sub>GEN</sub> :	= 6 Ω	27	44	ns
t <sub>f</sub>	Fall Time			5.8	12	ns
0	Total Gate Charge	$V_{GS} = 0 V to 10 V$		33	46	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 V to 5 V$	V <sub>DD</sub> = 75 V	18	26	nC
$Q_{gs}$	Total Gate Charge		I <sub>D</sub> = 9.6 A	7.9		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			7.7		nC

#### **Drain-Source Diode Characteristics**

V	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 2 \text{ A}$	(Note 2)	0.69	1.2	V
v <sub>SD</sub>	Source to Drain Diode 1 ofward voltage	$V_{GS} = 0 \text{ V}, I_{S} = 9.6 \text{ A}$	(Note 2)	0.77	1.3	'
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 9.6 A, di/dt = 100 A/μs		76	120	ns
Q <sub>rr</sub>	Reverse Recovery Charge			113	181	nC

<sup>1.</sup> R<sub>BJA</sub> is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>BJC</sub> is guaranteed by design while R<sub>BCA</sub> is determined by the user's board design.



a. 50 °C/W when mounted on a 1 in² pad of 2 oz copper



b.125 °C/W when mounted on a minimum pad of 2 oz copper

- 2. Pulse Test: Pulse Width < 300  $\mu s,$  Duty cycle < 2.0 %.
- 3.  $E_{AS}$  of 220 mJ is based on starting  $T_{J} = 25$  °C, L = 1 mH,  $I_{AS} = 21$  A,  $V_{DD} = 150$  V,  $V_{GS} = 10$  V. 100% test at L = 0.1 mH,  $I_{AS} = 46$  A.

### Typical Characteristics T<sub>.1</sub> = 25 °C unless otherwise noted

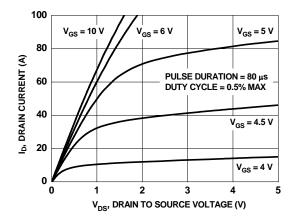


Figure 1. On-Region Characteristics

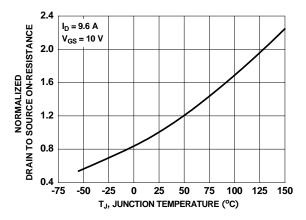


Figure 3. Normalized On-Resistance vs Junction Temperature

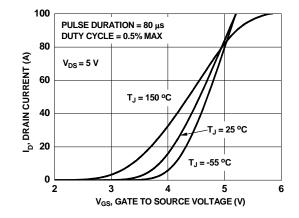


Figure 5. Transfer Characteristics

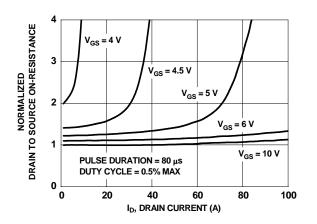


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

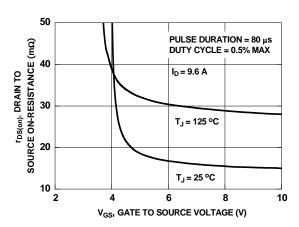


Figure 4. On-Resistance vs Gate to Source Voltage

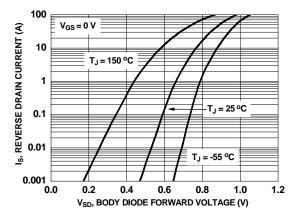


Figure 6. Source to Drain Diode **Forward Voltage vs Source Current** 

### **Typical Characteristics** $T_J = 25$ °C unless otherwise noted

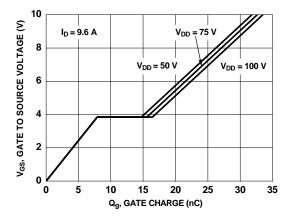


Figure 7. Gate Charge Characteristics

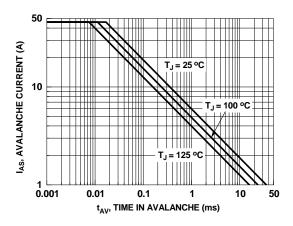


Figure 9. Unclamped Inductive Switching Capability

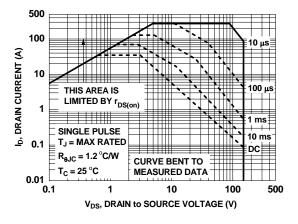


Figure 11. Forward Bias Safe Operating Area

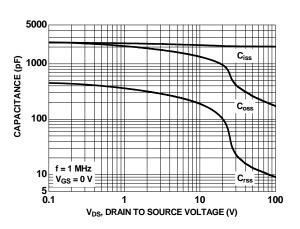


Figure 8. Capacitance vs Drain to Source Voltage

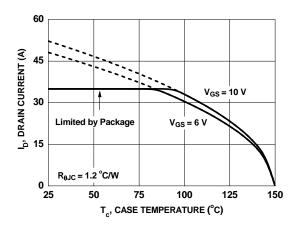


Figure 10. Maximum Continuous Drain Current vs Case Temperature

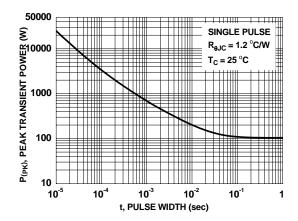


Figure 12. Single Pulse Maximum Power Dissipation

### **Typical Characteristics** $T_J = 25$ °C unless otherwise noted

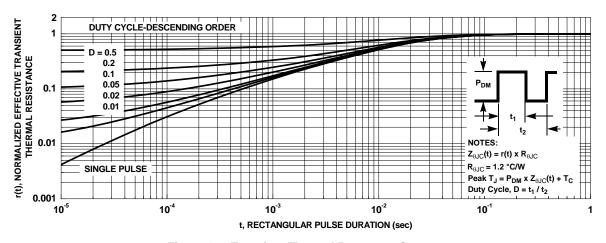
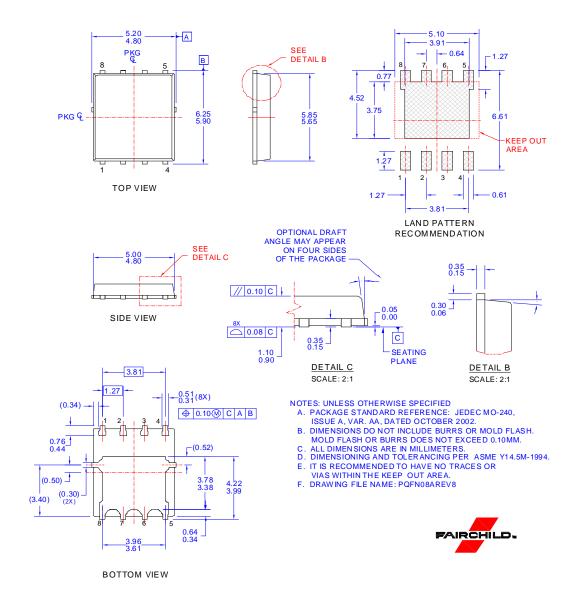


Figure 13. Transient Thermal Response Curve

#### **Dimensional Outline and Pad Layout**



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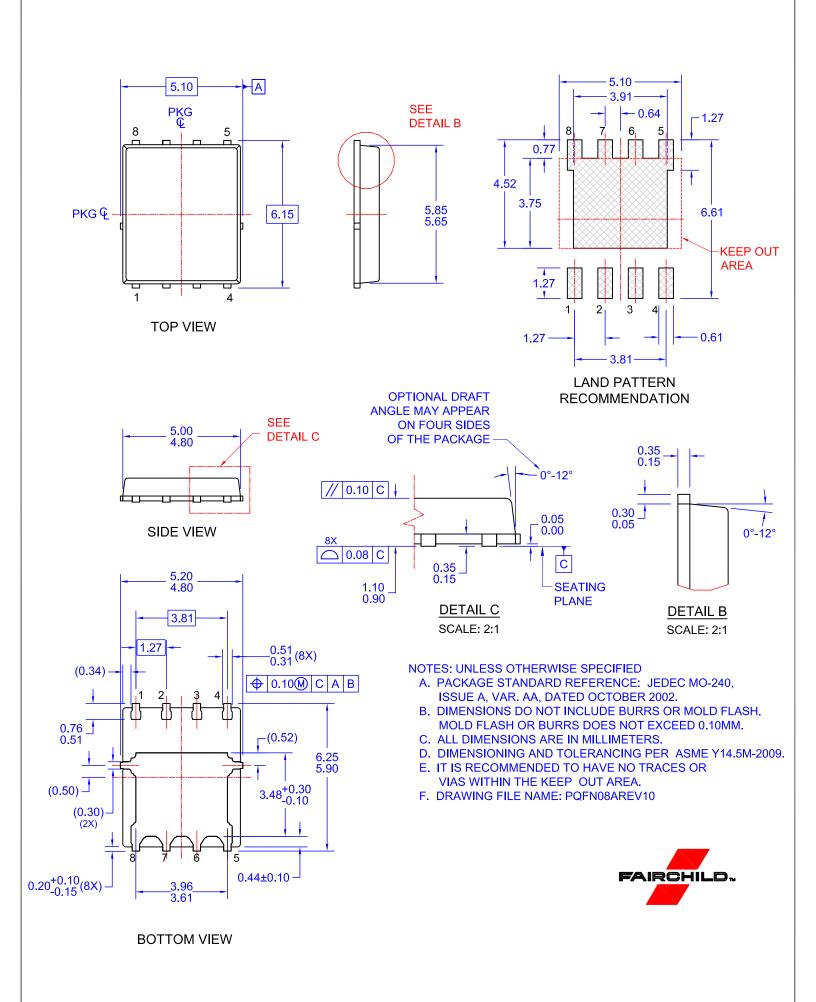
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